

### **Description**

The AO4801A uses advanced trench technology

and design to provide excellent RDS(ON) with low gat

e charge. It can be used in a wide variety of applications.



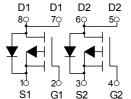
SOP-8

**General Features** 

 $V_{DS} = -30V, I_{D} = -5.3A$ 

 $R_{DS(ON)} < 42m$  @  $V_{GS}=-10V$ 

 $R_{DS(ON)} < 85m$  @  $V_{GS}=-4.5V$ 



## **Application**

PWM application

Load switch

**Dual P-Channel MOSFET** 

#### **Package Marking and Ordering Information**

Product ID	Pack	Brand	Qty(PCS)
AO4801A	SOP-8	HXY MOSFET	3000

#### Absolute Maximum Ratings (T<sub>A</sub>=25 ℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V <sub>DS</sub>	Drain-Source Voltage	-30	V
V <sub>G</sub> s	Gate-Source Voltage	±20	V
l <sub>D</sub>	Drain Current-Continuous	-5.3	Α
Ірм	Drain Current-Pulsed (Note 1)	-20	Α
P <sub>D</sub>	Maximum Power Dissipation	2.6	W
T <sub>J</sub> ,T <sub>STG</sub>	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}$ C
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)	49	°C/W



## Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

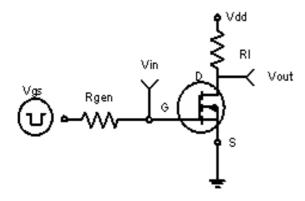
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =-250μA	-30	-33	-	V
Zero Gate Voltage Drain Current	loss	V <sub>DS</sub> =-24V,V <sub>GS</sub> =0V	-	_	-1	μΑ
Gate-Body Leakage Current	Igss	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	ı	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V <sub>GS</sub> (th)	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250µA	-1	-1.6	-3	V
		V <sub>GS</sub> =-10V, I <sub>D</sub> =-5.3A	-	35	42	mR
Drain-Source On-State Resistance	Rds(on)	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-4.2A	-	70	85	mR
Forward Transconductance	grs	V <sub>DS</sub> =-15V, I <sub>D</sub> =-4.5A	4	7	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C <sub>lss</sub>		-	540	-	PF
Output Capacitance	Coss	V <sub>DS</sub> =-15V,V <sub>GS</sub> =0V,	-	150	-	PF
Reverse Transfer Capacitance	Crss	F=1.0MHz	-	75	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	<b>t</b> d(on)		-	8	-	nS
Turn-on Rise Time	tr	V <sub>DD</sub> =-15V, ID=-1A,	-	14	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	V <sub>GS</sub> =-10V,R <sub>GEN</sub> =6	-	18	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	10	-	nS
Total Gate Charge	Qg		-	12	-	nC
Gate-Source Charge	Qgs	V <sub>DS</sub> =-15V,I <sub>D</sub> =-5.3A,V <sub>GS</sub> =-	-	2.4	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	3.2	-	nC
<b>Drain-Source Diode Characteristics</b>	1	I	1			
Diode Forward Voltage (Note 3)	Vsp	V <sub>GS</sub> =0V, I <sub>S</sub> =-5.3A	_	-	-1.2	V

#### Notes:

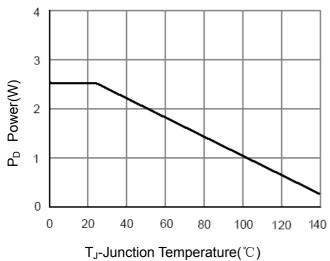
- $\textbf{1.} \ \textbf{Repetitive Rating: Pulse width limited by maximum junction temperature.}$
- **2.** Surface Mounted on FR4 Board,  $t \le 10$  sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



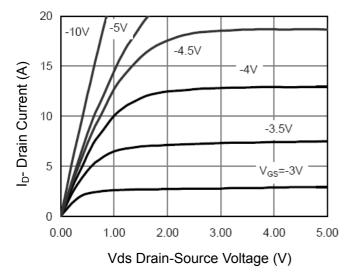
# **Typical Electrical and Thermal Characteristics**



**Figure 1:Switching Test Circuit** 



**Figure 3 Power Dissipation** 



**Figure 5 Output Characteristics** 

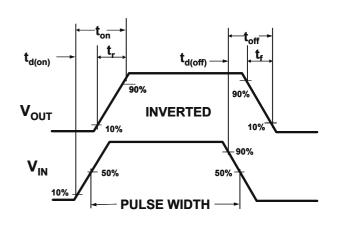
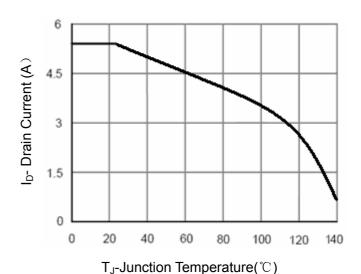


Figure 2:Switching Waveforms



**Figure 4 Drain Current** 

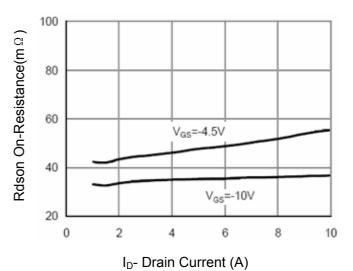
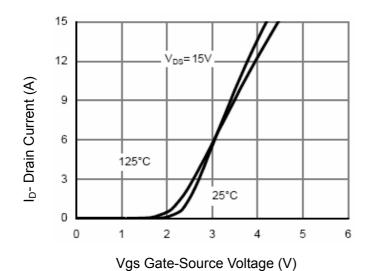
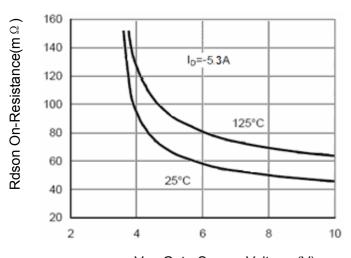


Figure 6 Drain-Source On-Resistance





**Figure 7 Transfer Characteristics** 



Vgs Gate-Source Voltage (V)
Figure 9 Rdson vs Vgs

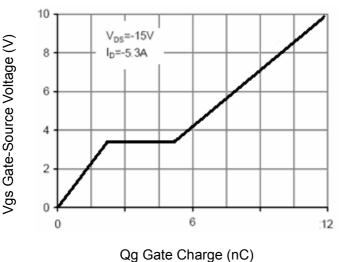


Figure 11 Gate Charge

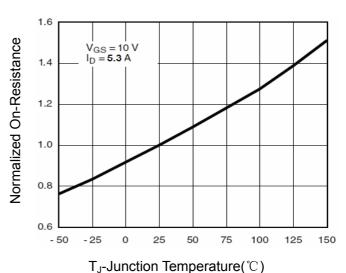


Figure 8 Drain-Source On-Resistance

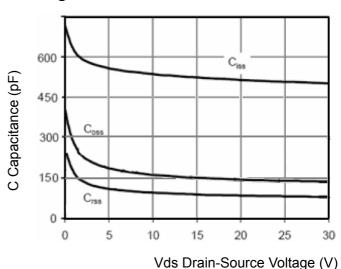
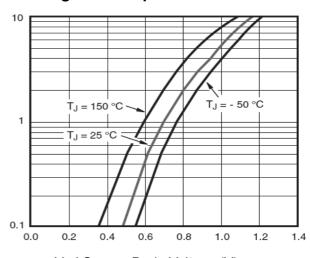


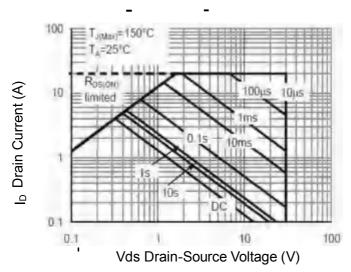
Figure 10 Capacitance vs Vds



Is- Reverse Drain Current (A)

Vsd Source-Drain Voltage (V)

Figure 12 Source- Drain Diode Forward



**Figure 13 Safe Operation Area** 

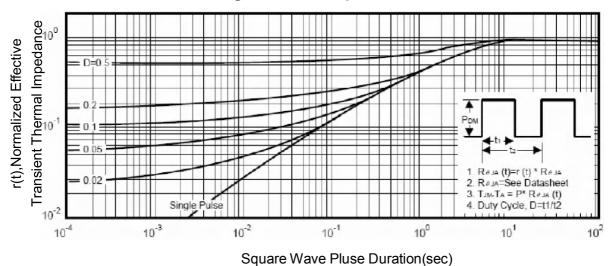
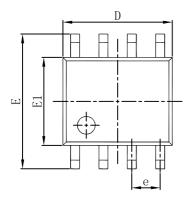


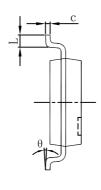
Figure 14 Normalized Maximum Transient Thermal

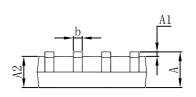
**Impedance** 



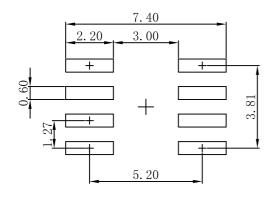
## **SOP-8 Package Outline Dimensions**







Symbol	Dimensions In Millimeters		Dimensions In Inches			
	Min	Max	Min	Max		
A	1.350	1.750	0.053	0.069		
A1	0.100	0. 250	0.004	0.010		
A2	1.350	1.550	0.053	0.061		
b	0.330	0.510	0.013	0.020		
c	0.170	0.250	0.007	0.010		
D	4.800	5.000	0.189	0. 197		
e	1. 270 (	1. 270 (BSC)		0.050 (BSC)		
E	5.800	6.200	0. 228	0. 244		
E1	3.800	4.000	0.150	0. 157		
L	0.400	1.270	0.016	0.050		
θ	0°	8°	0°	8°		



- Note: 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
  3.The pad layout is for reference purposes only.



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